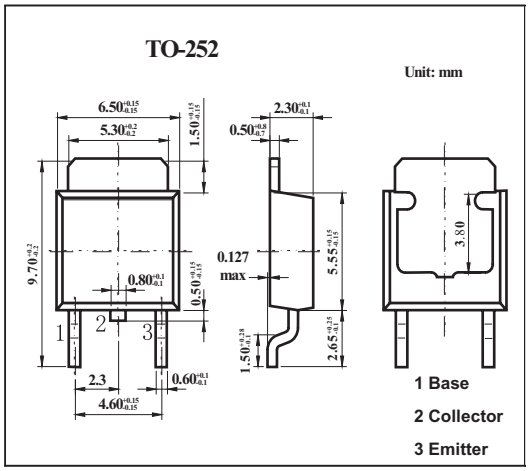
PNP Epitaxial Silicon Transistor

MJD350



■ Features

- Load Formed for Surface Mount Application
- Straight Lead

■ Absolute Maximum Ratings Ta = 25℃unless otherwise noted

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-300	V
Collector-Emitter Voltage	V_{CEO}	-300	V
Emitter-Base Voltage	V_{EBO}	-3	V
Collector Current (DC)	I_C	-0.5	A
Collector Current (Pulse)	I_{CP}	-0.75	A
Collector Dissipation (TC = 25℃)	P_C	15	A
Collector Dissipation (Ta = 25℃)		1.56	W
Junction Temperature	T_J	150	W
Storage Temperature	T_{STG}	-65 to 150	℃

■ Electrical Characteristics Ta = 25℃unless otherwise noted

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-Emitter Sustaining Voltage *	$V_{CEO(sus)}$	I_C = 1mA, I_B = 0	-300			V
Collector Cut-off Current	I_{CEO}	V_{CB} = -300V, I_E =0			-0.1	mA
Emitter Cut-off Current	I_{EBO}	V_{EB} = -3V, I_C = 0			-0.1	mA
DC Current Gain *	h_{FE}	V_{CE} = -10V, I_C = -50mA	30		240	

*Pulse Test: PW≤300μs, Duty Cycle≤2%